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Technical Program

MONDAY, JUNE 17, 1996

8:30 am–10:10 am
MCC 134

Session I: MMIC ADVANCES FOR MILITARY AND COMMERCIAL APPLICATIONS (Invited Session)

Chair: L. Liu, *TRW*

Co-chair: M. Kumar, *Loral Defense Systems*

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Chair: H.C. Huang, *COMTEX Corp*

Co-chair: I.J. Bahl, *ITT-GTC*

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Session III: SIGNAL GENERATION AND CONTROL

Chair: J. Mondal, *Northrop Grumman*

Co-chair: C. Chao, *Hughes Aircraft*

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Session IV: BiCMOS AND HBT MMIC TECHNOLOGIES

Chair: V. Nair, *Motorola PCRL*

Co-chair: J.M. Schellengerg, *Schellenberg Associates*

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Chair: A. Adar, *Anadigics*

Co-chair: F. Ali, *Westinghouse*

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Session VI: SMALL SIGNAL IC's & PASSIVE COMPONENTS

Chair: D. Lovelace, *Motorola, Inc.*

Co-chair: C. Keramarrec, *Analog Devices*

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Session VII: LOW NOISE MILLIMETER WAVE MMICs
(Joint with IMS)

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Session VIII: LARGE SIGNAL GENERATION AND AMPLIFICATION
(Joint with IMS)

Chair: N. Camilleri, *AMD*
Co-chair: Z. Bardai, *Hughes*

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Session IX: MMIC SYSTEMS COMPONENTS

(Joint with IMS)

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Co-chair: H.A. Hung

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2:30 pm–5:00 pm

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